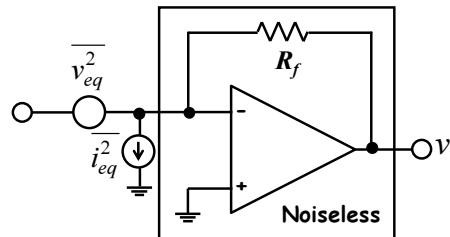


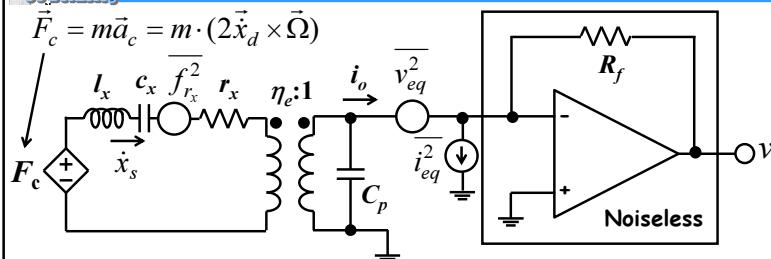
Lecture 25m: Noise & MDSExample: TransR Amplifier Noise (cont)

- To summarize, for a transresistance amplifier, the equivalent input-referred current and voltage noise generators are given by:

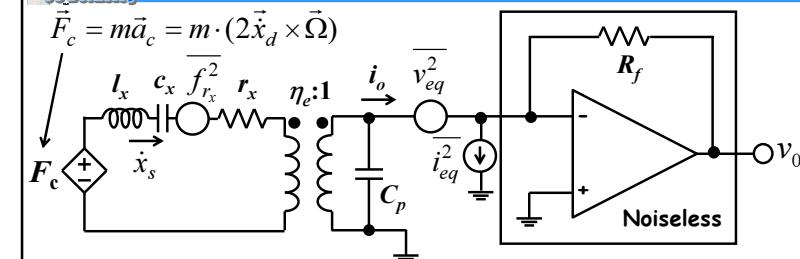


$$\overline{i_{eq}^2} = \overline{i_{ia}^2} + \overline{i_f^2} + \frac{\overline{v_{ia}^2}}{R_f^2}$$

$$\overline{v_{eq}^2} = \overline{v_{ia}^2}$$

Back to Gyro Noise & MDSExample: Gyro MDS Calculation

- The gyro sense presents a large effective source impedance
 - Currents are the important variable; voltages are "opened" out
 - Must compare i_o with the total current noise i_{eqTOT} going into the amplifier circuit

Example: Gyro MDS Calculation (cont)

- First, find the rotation to i_o transfer function:

$$\dot{x}_s = \frac{\omega_s Q_s}{k_s} \Theta_s(j\omega_d) F_s = \frac{\omega_s Q_s}{k_s} \cdot 2\omega_d \chi_d \Sigma m \cdot \Theta_s(j\omega_d)$$

$\boxed{F_s = F_c = 2\omega_d \chi_d \Sigma m}$

$$\dot{x}_s = 2 \frac{\omega_d}{\omega_s} Q_s \chi_d \Theta_s(j\omega_d) \cdot \Sigma$$

Lecture 25m: Noise & MDS

Example: Gyro MDS Calculation (cont)

$i_o = \eta_e \dot{x}_s = 2 \frac{w_d}{w_s} Q_x \chi_d \eta_e \Theta_s(j\omega_d) \cdot \dot{x}_s \rightarrow i_o = A \dot{x}_s$
Where $A = 2 \frac{w_d}{w_s} Q_x \chi_d \eta_e \Theta_s(j\omega_d)$
 $A \triangleq \text{scale factor}$

When $\dot{x}_s = \dot{x}_{s,\min} \triangleq \text{MDS}$, $i_o = i_{eq,TOT}$ input-referred noise current entering the sense amplifier \rightarrow in $\mu\text{A}/\sqrt{\text{Hz}}$

$$\therefore i_{eq,TOT} = A \dot{x}_{s,\min} \rightarrow \dot{x}_{s,\min} = \frac{i_{eq,TOT}}{A} \left(\frac{3600\pi}{\text{hr}} \right) \left(\frac{180^\circ}{\pi} \right) \left[(\%)/\sqrt{\text{Hz}} \right]$$

Angle Random Walk: $ARW = \frac{1}{60} \dot{x}_{s,\min} [\%/\text{hr}]$

Earlier to determine directional error as a function of elapsed time.

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Example: Gyro MDS Calculation (cont)

$\vec{F}_c = m \vec{a}_c = m \cdot (2 \vec{x}_d \times \vec{\Omega})$

$R_s: \text{large} \therefore N_r^2 \text{ "opened" out}$

- Now, find the $i_{eq,TOT}$ entering the amplifier input:

$$i_{eq,TOT} = i_s + i_{eq} \rightarrow i_{eq,TOT} = \frac{i_s^2}{R_f} + i_f^2 + i_{ia}^2 + \frac{N_r^2}{R_f^2} \quad \frac{f_{rx}^2}{\Delta f} = 4kT r_x$$

Brownian motion noise of the sense element \rightarrow determined entirely by the noise in $r_x \rightarrow f_{rx}^2$

easiest to convert to an all electrical equiv. ckt.

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Example: Gyro MDS Calculation (cont)

where $L_{rx} = \frac{r_x}{\eta_e^2}$, $C_{rx} = \eta_e^2 C_x$, $R_{rx} = \frac{r_x}{\eta_e^2}$

$$\therefore i_s = N_{Rx} \left(\frac{1}{R_x} \right) \Theta_s(j\omega_d) \rightarrow \frac{i_s^2}{\Delta f} = 4kT R_x \left(\frac{1}{R_x^2} \right) |\Theta_s(j\omega_d)|^2$$

$$\Rightarrow \frac{i_s^2}{\Delta f} = \frac{4kT}{R_x} |\Theta_s(j\omega_d)|^2$$

Thus:

$$\frac{i_{eq,TOT}^2}{\Delta f} = \frac{4kT}{R_x} |\Theta_s(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{i_{ia}^2}{\Delta f} + \frac{N_{ia}^2}{\Delta f} \left(\frac{1}{R_f^2} \right)$$

Learn to get these from EE240.
Or just get them from a data sheet ...

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LF356 Op Amp Data Sheet

LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (Bi-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Common Features

- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High input impedance: $10^{12}\Omega$
- Low input noise current: $0.01\text{ pA}/\sqrt{\text{Hz}}$
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

$\frac{i_{ia}^2}{\Delta f} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$

Features

Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Uncommon Features

	LF155/ LF355	LF156/ LF356	LF257/ LF357	Units
	4	1.5	1.5	μs
Extremely fast settling time to 0.01%	4	1.5	1.5	μs
Fast slew rate	5	12	50	V/μs
Wide gain bandwidth	2.5	5	20	MHz
Low input noise voltage	20	12	12	nV/√Hz

$\frac{i_{ia}^2}{\Delta f} = 12 \text{ nV}/\sqrt{\text{Hz}}$

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Lecture 25m: Noise & MDS

Example ARW Calculation

Example Design:

- Sensor Element:
 $m = (100\mu\text{m})(100\mu\text{m})(20\mu\text{m})(2300\text{kg/m}^3) = 4.6 \times 10^{-10}\text{kg}$
 $\omega_s = 2\pi(15\text{kHz})$
 $\omega_d = 2\pi(10\text{kHz})$
 $k_s = \omega_s^2 m = 4.09 \text{ N/m}$
 $x_d = 20 \mu\text{m}$
 $Q_s = 50,000$
 $V_p = 5\text{V}$
 $h = 20 \mu\text{m}$
 $d = 1 \mu\text{m}$
- Sensing Circuitry:
 $R_f = 100\text{k}\Omega$
 $i_{ia} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$
 $v_{ia} = 12 \text{ nV}/\sqrt{\text{Hz}}$

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Example ARW Calculation (cont)

Get rotation rate to output current scale factor:

$$A = 2 \frac{w_d}{\omega_s} Q_s \chi_d \eta_e |\Theta_s(j\omega_d)| = 2 \left(\frac{10\text{K}}{15\text{K}} \right) \left(50\mu\text{m} \right) \left(5 \right) \left(2000\epsilon_0 \right) \left(0.00024 \right) = 2.83 \times 10^{-12} \text{ C}$$

$$\Theta_s(j\omega_d) = \frac{(j\omega_d)(\omega_s/\omega_s)}{-\omega_d^2 + j\omega_d\omega_s + \omega_s^2} = \frac{j(10\text{K})(15\text{K})/(50\text{K})}{(15\text{K})^2 - (10\text{K})^2 + j(10\text{K})(15\text{K})/50\text{K}} = \frac{j(3\text{K})}{1.25 \times 10^8 + j(3\text{K})}$$

$$\Rightarrow |\Theta_s(j\omega_d)| = \frac{3\text{K}}{\sqrt{(1.25 \times 10^8)^2 + (3\text{K})^2}} = 0.000024 \quad 8.85 \times 10^{-8} \text{ F/m}$$

$$\frac{\partial C}{\partial x} = \frac{C_0}{d} = \frac{\epsilon_0 h W_p}{d} = \frac{\epsilon_0 (20\mu\text{m})(100\mu\text{m})}{(1\mu\text{m})^2} = 2000\epsilon_0 \rightarrow \eta_e = V_p \frac{\partial C}{\partial x} = S(2000\epsilon_0) \quad \text{Assume electrode covers the whole sidewall.} \quad 8.85 \times 10^{-12} \text{ F/m}$$

Then, get noise:

$$\frac{i_{eq,TOT}^2}{\Delta f} = \frac{4kT}{R_f} |\Theta_s(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{i_{ia}^2}{R_f} + \frac{V_{ia}^2}{R_f^2} \left(\frac{1}{\Delta f} \right)$$

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Example ARW Calculation (cont)

$R_{eq} = \frac{w_s m}{Q_s \eta_e^2} = \frac{2\pi(15\text{K})(4.6 \times 10^{-10})}{(50\text{K})(8.85 \times 10^{-8})^2} = 110.6 \text{ k}\Omega$

$$\frac{i_{eq,TOT}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6\text{K})} (0.000024)^2 + \frac{(1.66 \times 10^{-29})}{1\text{M}} + (0.01\text{p})^2 + \frac{(12\text{n})^2}{(1\text{M})^2}$$

$$\xrightarrow{\text{Sensor element noise insignificant}} 8.64 \times 10^{-25} \text{ A}^2/\text{Hz} \quad \xrightarrow{\text{Noise from R}_f \text{ dominates!}} 1.66 \times 10^{-26} \text{ A}^2/\text{Hz} \quad \xrightarrow{\text{Noise from R}_f \text{ dominates!}} 1.44 \times 10^{-28} \text{ A}^2/\text{Hz}$$

$$\therefore \frac{i_{eq,TOT}^2}{\Delta f} = 1.68 \times 10^{-26} \text{ A}^2/\text{Hz} \rightarrow i_{eq,TOT} = \sqrt{\frac{i_{eq,TOT}^2}{\Delta f}} = 1.30 \times 10^{-13} \text{ A}/\sqrt{\text{Hz}}$$

$$\therefore \sigma_{min} = \frac{i_{eq,TOT}}{A} \left(\frac{3600\pi}{\text{hr}} \right) \left(\frac{180^\circ}{\pi} \right) = \frac{1.30 \times 10^{-13}}{2.83 \times 10^{-12}} (3600) \left(\frac{180^\circ}{\pi} \right) = 9448 (\%/\text{hr})/\sqrt{\text{Hz}}$$

And finally:
 $ARW = \frac{1}{60} \sigma_{min} = \frac{1}{60} (9448) = 157 \%/\text{hr} = ARW$ \Rightarrow Almost turned around in 1 hour!

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What if $\omega_d = \omega_s$?

If $\omega_d = \omega_s = 15\text{kHz}$, then $|\Theta_s(j\omega_d)| = 1$ and

$$A = 2 \frac{w_d}{\omega_s} Q_s \chi_d \eta_e |\Theta_s(j\omega_d)| = 2 Q_s \chi_d \eta_e = 2(50\mu\text{m})(20\mu\text{m})(5)(2000\epsilon_0) = 1.77 \times 10^{-7} \text{ C}$$

$$\frac{i_{eq,TOT}^2}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6\text{K})} (1)^2 + \frac{(1.66 \times 10^{-29})}{1\text{M}} + (0.01\text{p})^2 + \frac{(12\text{n})^2}{(1\text{M})^2}$$

$$\xrightarrow{\text{Now, the sensor element dominates!}} 1.51 \times 10^{-25} \text{ A}^2/\text{Hz} \quad 1.66 \times 10^{-26} \text{ A}^2/\text{Hz} \quad 1 \times 10^{-28} \text{ A}^2/\text{Hz} \quad 1.44 \times 10^{-28} \text{ A}^2/\text{Hz}$$

$$\therefore \frac{i_{eq,TOT}^2}{\Delta f} = 1.67 \times 10^{-25} \text{ A}^2/\text{Hz} \rightarrow i_{eq,TOT} = \sqrt{\frac{i_{eq,TOT}^2}{\Delta f}} = 4.08 \times 10^{-13} \text{ A}/\sqrt{\text{Hz}}$$

$$\therefore \sigma_{min} = \frac{i_{eq,TOT}}{A} \left(\frac{3600\pi}{\text{hr}} \right) \left(\frac{180^\circ}{\pi} \right) = \frac{4.08 \times 10^{-13}}{1.77 \times 10^{-7}} (3600) \left(\frac{180^\circ}{\pi} \right) = 0.476 (\%/\text{hr})/\sqrt{\text{Hz}}$$

And finally:
 $ARW = \frac{1}{60} \sigma_{min} = \frac{1}{60} (0.476) = 0.0079 \%/\text{hr} = ARW$ \Rightarrow Navigation grade!

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